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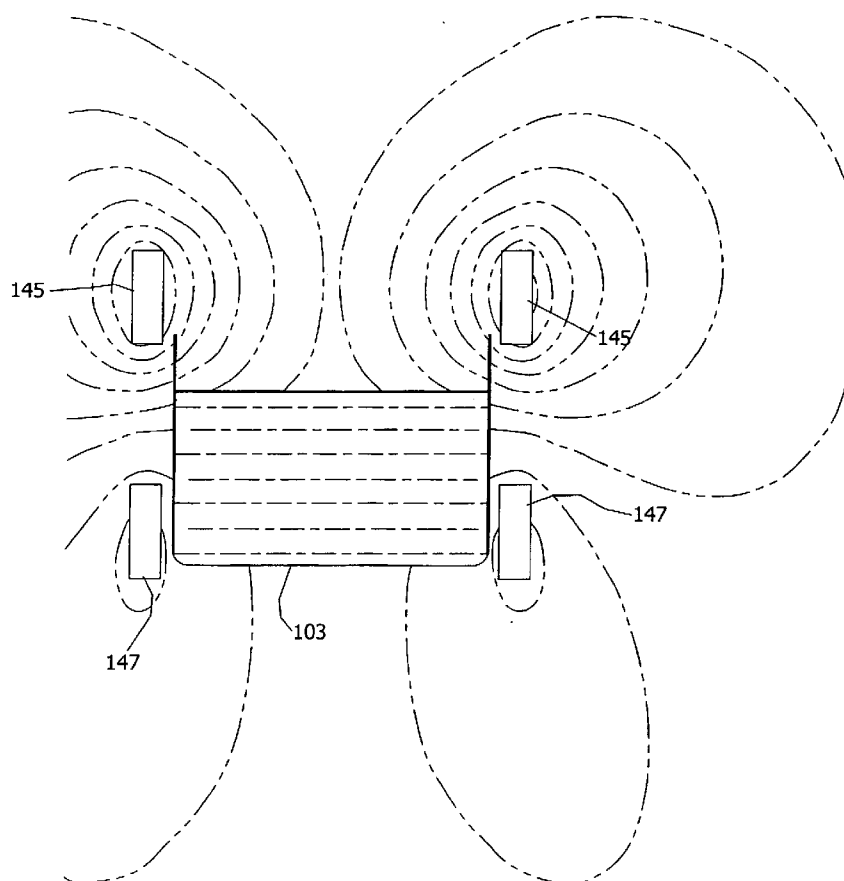
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(54) Title: CONTROLLING MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING A VARIABLE MAGNETIC FIELD



(57) Abstract: Methods and system for controlling crystal growth in a Czochralski crystal growing apparatus. A magnetic field is applied within the crystal growing apparatus and varied to control a shape of the melt-solid interface where the ingot is being pulled from the melt. The shape of the melt-solid interface is formed to a desired shape in response to the varied magnetic field as a function of a length of the ingot.

WO 2006/073614 A1



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